

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
150V	6.9m Ω @10V	110A

Feature

- Fast Switching
- Low Gate Charge and Rdson
- 100% Single Pulse avalanche energy Test

Applications

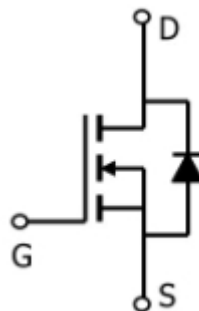
- Power switching application
- DC-DC Converter
- Power Management

Package

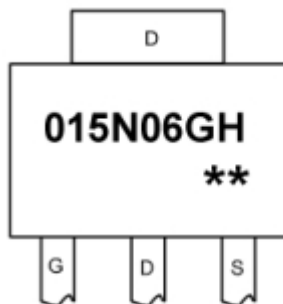


TO-220F(1:G 2:D 3:S)

Circuit diagram



Marking



015N06GH : Product code
****** : Week code

Absolute maximum ratings

(T_a=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	150	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous drain current (T _C = 25°C)	I _D	110	W
Pulsed Drain Current	I _{DM}	440	A
Power Dissipation (T _C = 25°C)	P _D	375	W
Single Pulse Avalanche Energy ¹	E _{AS}	1056	mJ
Thermal Resistance Junction- Case	R _{θJC}	0.33	°C/ W
Operation and storage temperature	T _{STG} , T _J	-55~ +150	°C

Electrical characteristics

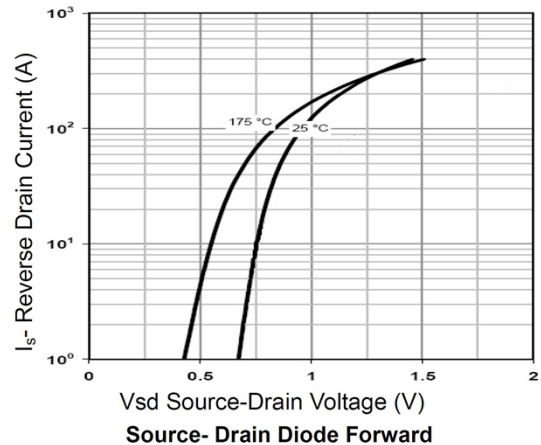
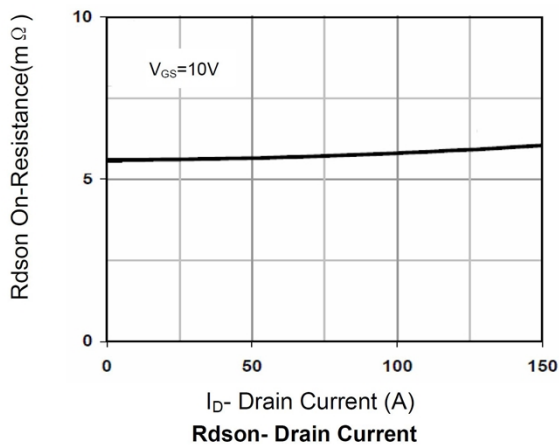
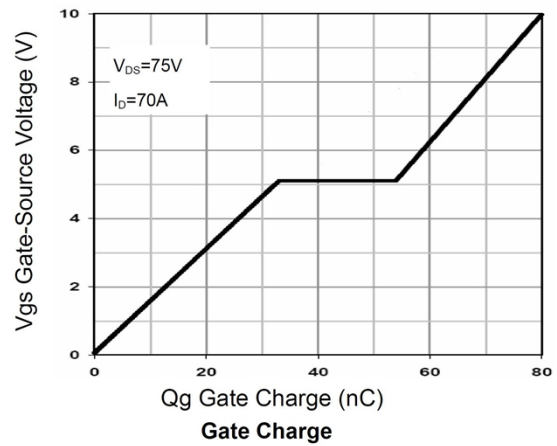
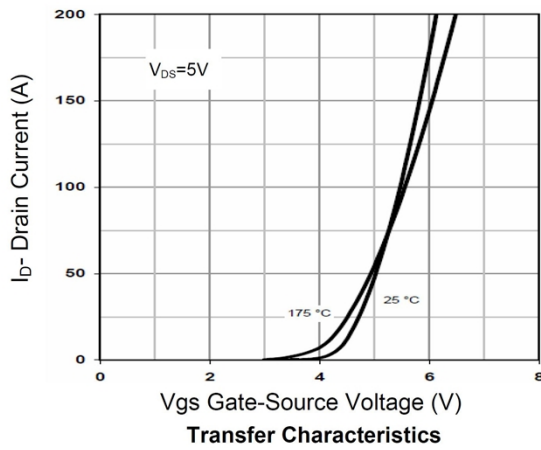
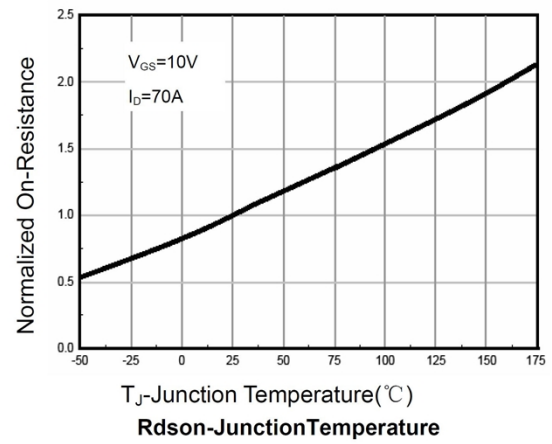
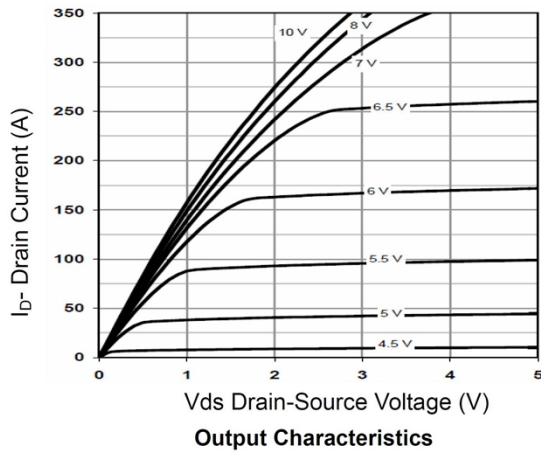
(T_A=25°C, unless otherwise noted)

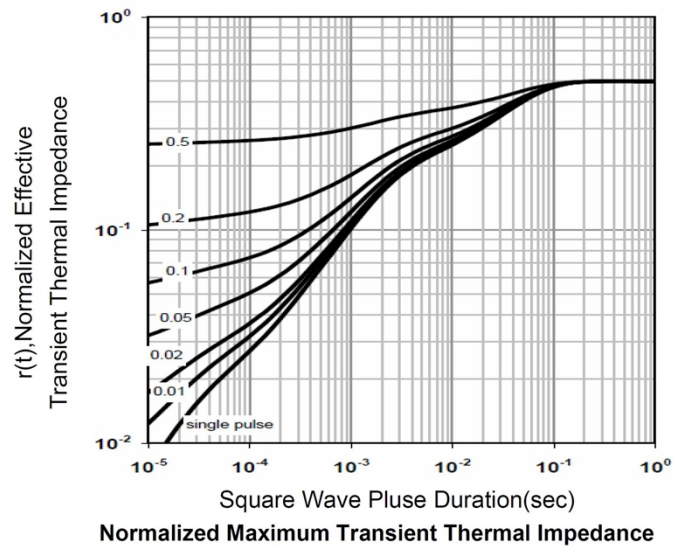
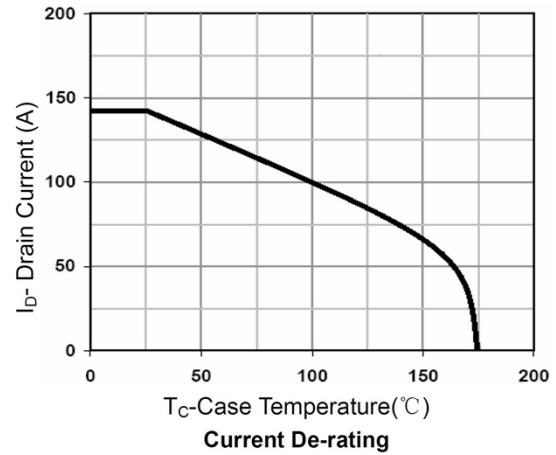
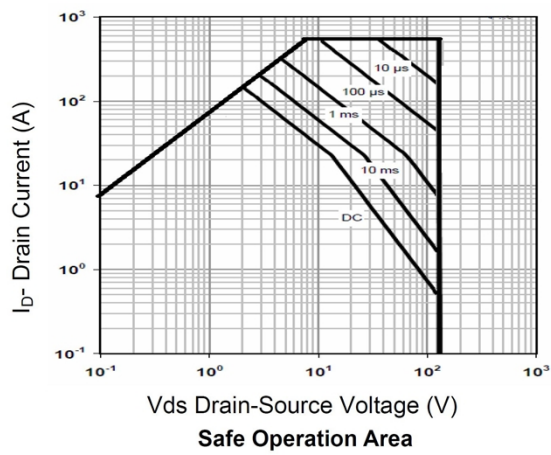
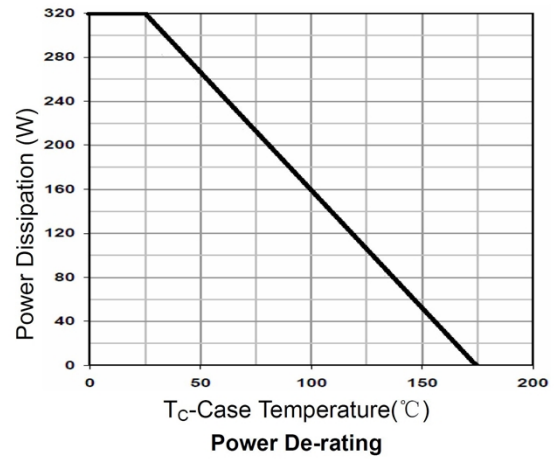
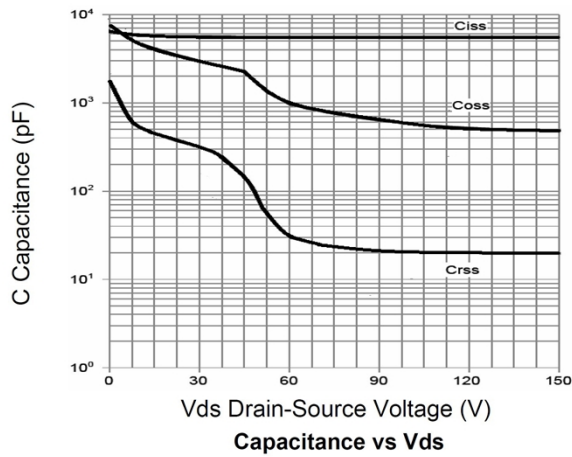
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	150			V
Drain Cut-Off Current	I _{DSS}	V _{DS} =120V,V _{GS} = 0V			1	uA
Gate-body leakage current	I _{GSS}	V _{GS} =±20V , V _{DS} =0V			±0.1	uA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	3	4	V
Drain-Source ON Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A		6.9	8.7	Ω
Dynamic characteristics ⁴						
Input Capacitance	C _{iss}	V _{DS} =75V,V _{GS} =0V, f=1MHz		5280		pF
Output Capacitance	C _{oss}			653		
Reverse Transfer Capacitance	C _{rss}			24		
Switching Characteristics						
Total Gate Charge(4.5V)	Q _g	V _{DS} =75V, V _{GS} =10V, I _D =70A		80		nC
Gate-Source Charge	Q _{gs}			33		
Gate-Drain Charge	Q _{gd}			21		
Turn-On Delay Time	T _{d(on)}	V _{GS} =10V, V _{DS} =75V, R _L =3Ω, R _G =4.7Ω		26		nS
Rise Time	T _r			35		
Turn-Off Delay Time	T _{d(off)}			45		
Fall Time	T _f			17		
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 1A, V _{GS} = 0V			1.2	V

Note :

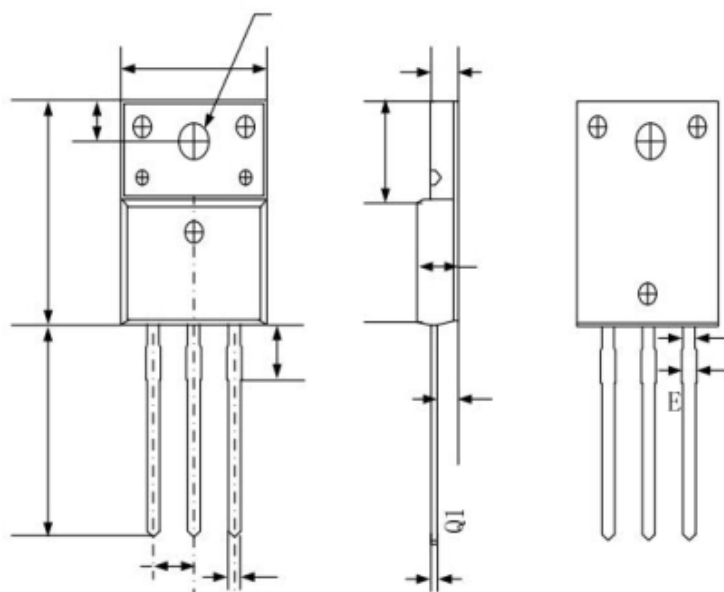
1. E_{AS} is tested at starting T_J = 25°C, V_{DD} =75V, V_{GS} = 10V, L = 0.5mH, R_G=25Ω ;

Typical Characteristics





TO-220F Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.50	4.83	0.18	0.19
b	0.70	0.91	0.03	0.04
b1	1.20	1.47	0.05	0.06
b2	1.10	1.38	0.04	0.05
c	0.45	0.63	0.02	0.02
D	15.67	16.07	0.62	0.63
e	2.54 BSC		0.10 BSC	
E	9.96	10.36	0.39	0.41
F	2.34	2.74	0.09	0.11
G	6.48	6.90	0.26	0.27
L	12.68	13.30	0.50	0.52
L1	3.13	3.50	0.12	0.14
Q	2.56	2.93	0.10	0.12
Q1	3.20	3.40	0.13	0.13
ΦR	3.08	3.28	0.12	0.13